### Optimization of few-layer black phosphorus for low-temperature magneto-transport studies

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# Black phosphorus

Layered structure with orthorhombic symmetry



Fig. 1 The chemical structures of the compounds in this study. (A) The orthorhombic unit cell of black phosphorus<sup>19</sup> (a = 3.31 Å, b = 4.38 Å c = 10.50 Å,  $\alpha = \beta = \gamma = 90^{\circ}$ ; space group *Bmab*; Crystallography Open Database ID: 1010325) which generates a layer structure comprising corrugated lamellae of phosphorus atoms held together by weak interlayer forces. (B) Three-layer phosphorene.

Cell parameters a=3.13Å b=10.47Å c=4.37Å

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J. R. Brent et al., Chem. Commun. 50 (2014) 13338.



# The renaissance of black phosphorus

- In 1914 first successful synthesis (Bridgman) and in 2007 synthesis at room pressure (Lange, Nilges)
- p-type semiconductor: 0.3eV direct band gap and high hole mobility (64,000 cm<sup>2</sup>/Vs @ 20 K)
- 1983 (Narita): n-type doping by Te
- 2014: First publications on bP layered thin films
- Highly reactive in air
- Band-gap tunable with layer number
- In-plane anisotropy of optical and transport properties

A. Morita, Appl. Phys. A 39 (1986) 227, S. Das et al., Nano Lett. 14 (2014) 5733,
F. Xia et al., Nat. Comm. 5 (2014) 4458,
A. Castellanos-Gomez et al., 2D Mater. 1 (2014) 025001





# **bP** exfoliation

 Liquid exfoliation of bP in dimethylsulfoxide (DMSO)



Adv. Mater. Interfaces 2016, 3, 1500441

Direct exfoliation in a polymer matrix



Chem. Mater., DOI: 10.1021/acs.chemmater.7b05298

Mechanical exfoliation

### bP flake surface science





h ~ 25 nm

# STM imaging of bP flakes exfoliated on graphene



Abhishek Kumar et al., J. Phys. Chem. C, submitted.



Abhishek Kumar et al., J. Phys. Chem. C, submitted.



### Crater alignment





Abhishek Kumar et al., J. Phys. Chem. C, submitted.



### Crater alignment





*c* = [001] (armchair)

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Abhishek Kumar et al., J. Phys. Chem. C, submitted.

### bP devices





# **bP Field Effect Transistor**





PMMA MMA Ti/Au contacts bP flake HMDS SiO<sub>2</sub> thermal oxide Si





R<sub>xx</sub>: 1-2 R<sub>xy</sub>: 1-3

Flake thickness:  $65 \pm 2 \text{ nm}$ 

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N. Hemsworth et al., Phys. Rev. B 94, 245404 (2016).



# **Transport Characterization**



N. Hemsworth et al., Phys. Rev. B 94, 245404 (2016).

•  $p \sim V_g$  for  $V_g < -30$  V

$$p = 10^{13} \text{ cm}^{-2} \text{ for } V_g = -30 \text{ V}$$

- Field-effect mobility μ: 300 cm<sup>2</sup>/Vs at V<sub>g</sub> = -70 V
- Negligible T-dependence in μ for 0.26 K < T < 20 K</li>





N. Hemsworth et al., Phys. Rev. B 94, 245404 (2016).





# Weak Localization

Weak localization is a quantum effect related to coherent scattering at low temperatures.



Picture from Bergmann, Weak localization in thin films, Physics Reports 107, 1984





Weak Localization

$$\Delta \sigma = -\frac{e^2}{2\pi^2 \hbar} \left( \Psi \left( \frac{1}{2} + \frac{B_1}{B} \right) - \Psi \left( \frac{1}{2} + \frac{B_2}{B} \right) + \frac{1}{2} \Psi \left( \frac{1}{2} + \frac{B_3}{B} \right) - \frac{1}{2} \Psi \left( \frac{1}{2} + \frac{B_2}{B} \right) \right), \quad (1)$$

where  $\Psi$  is the digamma function. The field parameters in the above expression are given by:

$$B_{1} = B_{0} + B_{\phi} + B_{\phi}$$
(2)  

$$B_{2} = \frac{4}{3}B_{so} + \frac{2}{3}B_{s} + B_{\phi}$$
(3)  

$$B_{3} = 2B_{s} + B_{\phi}$$
(4)

S. Hikami, A. I. Larkin, and Y. Nagaoka, Prog. Of Theor. Phys. 63 (1980) 707.



### Weak Localization



T = 0.26 K



N. Hemsworth et al., Phys. Rev. B 94, 245404 (2016).



N. Hemsworth *et al.*, Phys. Rev. B **94**, 245404 (2016).

NIC C57



Scattering Lengths

- Ballistic transport:  $\tau_{\varphi} \propto T^{-2}$
- Diffusive transport ( $\tau_0 < \tau_{\varphi}$ ):

Dephasing length vs. inelastic scattering time:

 $L_{\varphi} = \sqrt{D\tau_{\varphi}}$  with *D* diffusion coefficient

$$au_{arphi} \propto T^{-1}$$
 or  $L_{arphi} \propto T^{-1/2}$ 

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Lin and Bird, Jour. Phys. Cond. Mat. 14, R501, (2002)



N. Hemsworth et al., Phys. Rev. B 94, 245404 (2016).





N. Hemsworth et al., Phys. Rev. B 94, 245404 (2016).





### Quasi-1D systems

VOLUME 86, NUMBER 9

#### PHYSICAL REVIEW LETTERS

26 February 2001

#### **Geometry-Dependent Dephasing in Small Metallic Wires**

D. Natelson, R. L. Willett, K. W. West, and L. N. Pfeiffer

Bell Laboratories, Lucent Technologies, Murray Hill, New Jersey 07974 (Received 19 June 2000)

Temperature dependent weak localization is measured in metallic nanowires in a previously unexplored size regime down to width w = 5 nm. The dephasing time,  $\tau_{\phi}$ , shows a low temperature T dependence close to quasi-1D theoretical expectations ( $\tau_{\phi} \sim T^{-2/3}$ ) in the narrowest wires, but exhibits a relative saturation as  $T \rightarrow 0$  for wide samples on the same material as observed previously. As only

sample geometry is varied to exhibit constraint on models of dephasing

PHYSICAL REVIEW B, VOLUME 64, 121404(R)

#### Phase-coherent transport in ropes of single-wall carbon nanotubes

J. Appenzeller, R. Martel, and Ph. Avouris IBM T. J. Watson Research Center, Yorktown Heights, New York 10598

H. Stahl, U. Th. Hunger, and B. Lengeler II. Physikalisches Institut, RWTH Aachen, Templergraben 55, 52056 Aachen, Germany (Received 21 May 2001; revised manuscript received 23 July 2001; published 6 September 2001)

To study the phase breaking scattering events in single-wall carbon nanotubes (SWNTs), ropes of SWNTs are intentionally damaged by Ar<sup>+</sup> ion milling. Due to this treatment, the average distance an electron can travel before being elastically scattered is reduced to about 10 nm. This significantly increases the probability of one-dimensional localization and allows us to obtain the phase coherence angth ( $L_{\Phi}$ ) in ropes of SWNTs as a function of temperature. We find that Nyquist scattering ( $\tau_{\Phi} \sim T^{-2/3}$ ) as well as another dephasing mechanism with a  $\tau_{\Phi} \sim T^{-1}$  dependence are involved in limit of the phase-coherence transport. We also investigate the scattering of hot electrons in the system. The results support the statement that two different scattering mechanisms dominate the phase coherence length for different rope samples.



### Comparison with quasi-1D wires



N. Hemsworth et al., Phys. Rev. B 94, 245404 (2016).



### Strong anisotropic in-plane magnetotransport in a few-layer bP FET



F. Telesio et al., unpublished.

### bP / PMMA hybrid material





# bP embedded in PMMA

### prepared by in situ polymerization



F. Telesio et al., Nanotechnology, submitted.



### Optical microscopy and Raman spectroscopy





### **Transport properties**



F. Telesio et al., Nanotechnology, submitted.



### SEM + EDX



F. Telesio et al., Nanotechnology, submitted.



F. Telesio et al., Nanotechnology, submitted.





### Coworkers



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# Funding







### Thank you for your attention!